TOSHIBA TRANSISTOR SILICON EPITAXIAL PLANAR TYPE

HN2V02H

AM RADIO BAND TUNING APPLICATIONS.

High Capacitance Ratio: C1V/C8V=19.5 (Typ.)

High Q : Q = 200 (Min.)

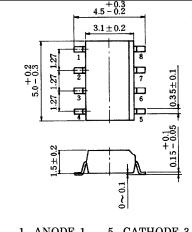
Including Three Devices in FM8 Package (Flat Pack Mini 8Pin)

Low Voltage Operation : $V_R = 1 \sim 8V$

MAXIMUM RATINGS (Ta = 25° C) (D₁, D₂, D₃)

| , , , , , | 2, 3, | | |
|---------------------------|--------------|---------|----------------------|
| CHARACTERISTIC | SYMBOL | RATING | UNIT |
| Reverse Voltage | v_{R} | 16 | V |
| Junction Temperature | T_{j} | 125 | °C |
| Storage Temperature Range | $T_{ m stg}$ | -55~125 | $^{\circ}\mathrm{C}$ |

Unit in mm



1. ANODE 1 5. CATHODE 3 2, 3. ANODE 2 6, 7. CATHODE 2

4. ANODE 3 8. CATHODE 1

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|--------------|-----------------|
| JEDEC | _ |
| EIAJ | _ |
| TOSHIBA | 1-5J1C |

Weight: 0.05g

ELECTRICAL CHARACTERISTICS (Ta = 25° C) (D₁, D₂, D₃)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|-------------------|------------------|-------------------------|------|------|------|------|
| Reverse Voltage | $v_{ m R}$ | $I_R = 10 \mu A$ | 16 | _ | _ | V |
| Reverse Current | $I_{\mathbf{R}}$ | $V_R = 16V$ | _ | _ | 20 | nA |
| Capacitance | C1V | $V_R=1V$, $f=1MHz$ | 435 | _ | 540 | рF |
| Capacitance | C3V | $V_R=3V$, $f=1MHz$ | 140 | _ | 250 | рF |
| Capacitance | C5V | $V_R=5V$, $f=1MHz$ | 50.0 | _ | 90.0 | pF |
| Capacitance | C8V | $V_R=8V$, $f=1MHz$ | 19.9 | _ | 26.7 | pF |
| Capacitance Ratio | C1V/C8V | _ | 16.2 | 19.5 | _ | _ |
| Figure of Merit | Q | $V_R = 1V$, $f = 1MHz$ | 200 | _ | _ | _ |

Note 1: Three Devices in one Package are matched for capacitance to 2.5%.

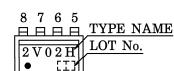
$$\frac{\text{C (Max.)} - \text{C (Min.)}}{\text{C (Min.)}} \leq 0.025 \, (\text{V}_{\text{R}} = 1 \sim 8\text{V})$$

Note 2: C8V is devided into two classifications as follows.

| Classification | C8V (pF) |
|----------------|-----------|
| A | 19.9~23.7 |
| В | 22.4~26.7 |

PIN ASSIGNMENT (TOP VIEW)





MARKING

1 2 3

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